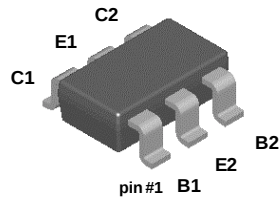


FMBA56



SuperSOT™-6
Mark: .2G
Dot denotes pin #1

PNP Multi-Chip General Purpose Amplifier

This device is designed for general purpose amplifier applications at collector currents to 300 mA. Sourced from Process 73.

Absolute Maximum Ratings*

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CES}	Collector-Emitter Voltage	80	V
V_{CBO}	Collector-Base Voltage	80	V
V_{EBO}	Emitter-Base Voltage	4.0	V
I_C	Collector Current - Continuous	500	mA
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
- 3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Characteristic	Max	Units
		FMBA56	
P_D	Total Device Dissipation	700	mW
	Derate above 25°C	5.6	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	180	$^\circ\text{C/W}$

PNP Multi-Chip General Purpose Amplifier
(continued)

Electrical Characteristics TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 1.0\text{ mA}, I_B = 0$	80			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 100\text{ }\mu\text{A}, I_E = 0$	80			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 100\text{ }\mu\text{A}, I_C = 0$	4.0			V
I_{CEO}	Collector-Cutoff Current	$V_{CE} = 60\text{ V}, I_B = 0$			0.1	μA
I_{CBO}	Collector-Cutoff Current	$V_{CB} = 80\text{ V}, I_E = 0$			0.1	μA

ON CHARACTERISTICS

h_{FE}	DC Current Gain	$I_C = 10\text{ mA}, V_{CE} = 1.0\text{ V}$ $I_C = 100\text{ mA}, V_{CE} = 1.0\text{ V}$	100 100			
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 100\text{ mA}, I_B = 10\text{ mA}$			0.25	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = 100\text{ mA}, V_{CE} = 1.0\text{ V}$			1.2	V

SMALL SIGNAL CHARACTERISTICS

f_T	Current Gain - Bandwidth Product	$I_C = 100\text{ mA}, V_{CE} = 1.0\text{ V},$ $f = 100\text{ MHz}$	50			MHz
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*Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$

NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors.

Spice Model

PNP (Is=12.27p Xti=3 Eg=1.11 Vaf=100 Bf=91.63 Ne=1.531 Ise=12.27p Ikf=1.009 Xtb=1.5 Br=1.287 Nc=2 Isc=0 Ikr=0 Rc=.6 Cjc=48.28p Mjc=.5615 Vjc=.75 Fc=.5 Cje=106.7p Mje=.5168 Vje=.75 Tr=496.3n Tf=865.8p Itf=.2 Vtf=2 Xtf=.8 Rb=10)

Typical Characteristics

